MITSUBISHI ELECTRIC
Changes for the Better

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Dear Sales Offices Team

[Notification] SiRF product high power Module - Multi sourcing on material

Thank you for your great supports on SiRF business.

We annouce that we adopt the multi sourcing of materials on the particular SiRF module product, as below.

We are sorry for the inconvenience caused on making announcement often, but your fully understanding and support woule be highly apprecaited.

Sincerely

Note

Summary of Reports

We have decided to purchase the diodes, that can support moderating the Pout-Vgg characteristic curve, from multiple suppliers. We are still facing the very critical situation on purchasing the diodes material that is used on the module RA60H3847M1, from the current supplier. It is caused by the one of global shortage of the components we are facing on several materials.

Therefore, we will start to purchase the diodes from multiple suppliers soon, so that we can be flexible on capturing those materials.

- **Applicable product** : RA60H3847M1-501

- **Schedule**

  ES: August 2022 ➔ Please inform if it is needed for the customers.

  MP: October 2022 (Subject to change depending on delivery timing)

- **Specifications** : There are no changes to the guarantees, reliability, and outline.
  We keep using the same part number.

- **Equivalent circuit diagram around diode**

  Fig.1 shows the equivalent circuit around diode.

  Fig.2 shows the Pout-Vgg characteristics with diode and without diode. The Pout-Vgg characteristics curve is moderated by adding diode.

- **Characteristics**

  Fig.3 shows the comparison of RF characteristics of RA60H3847M1-501, in using current diode and Multi-source diode. It shows the equal RF characteristics on the products that are used by both diodes.

Fig.1 Equivalent circuit diagram around diode

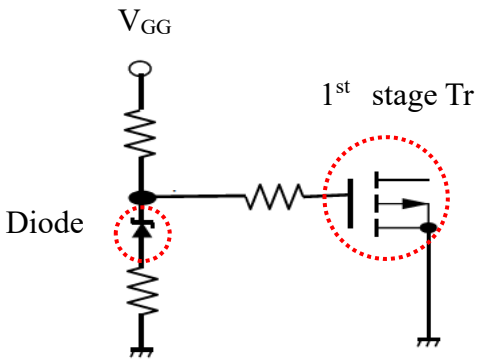

Fig.2 Pout-Vgg characteristics with diode and without diode

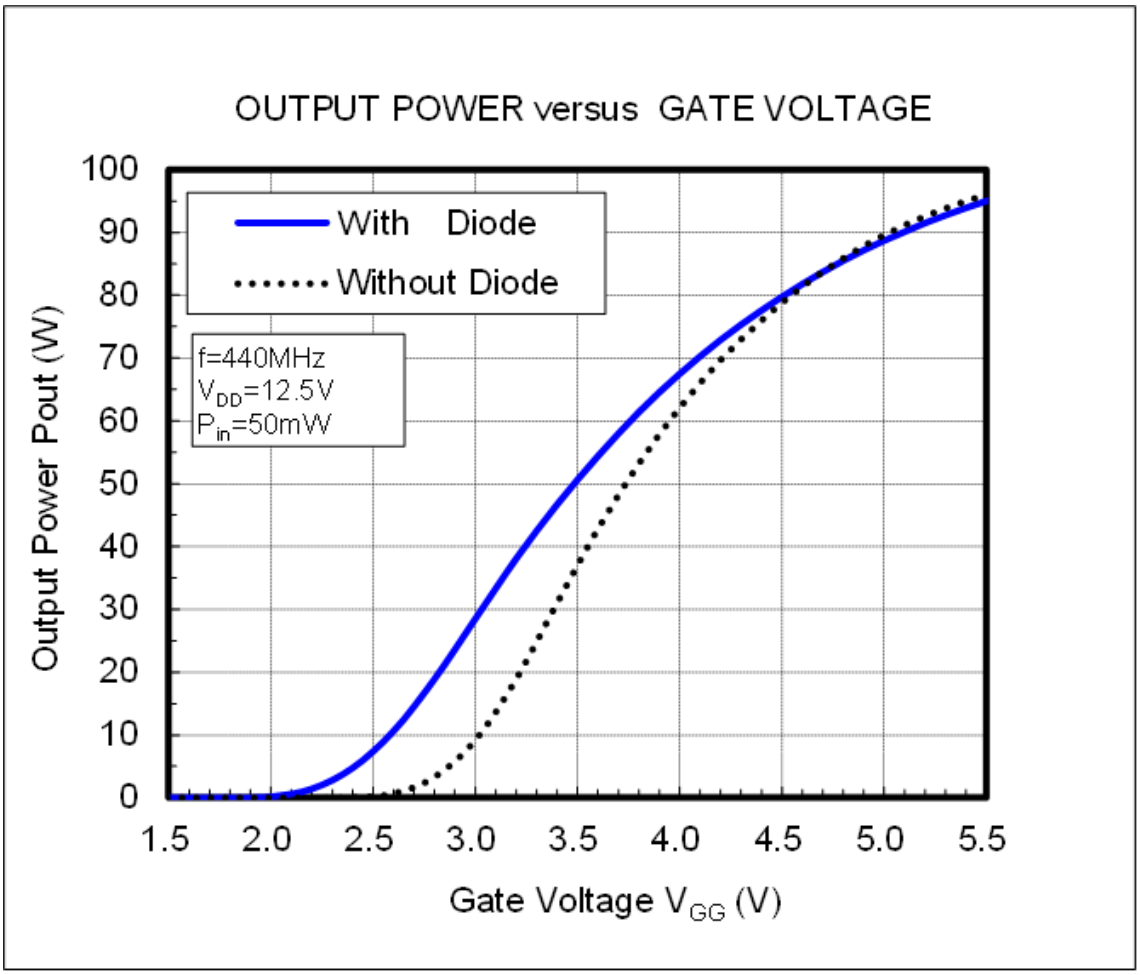

Fig.3-1 RF characteristics of RA60H3847M1-501 (Current diode, Multi-source diode)

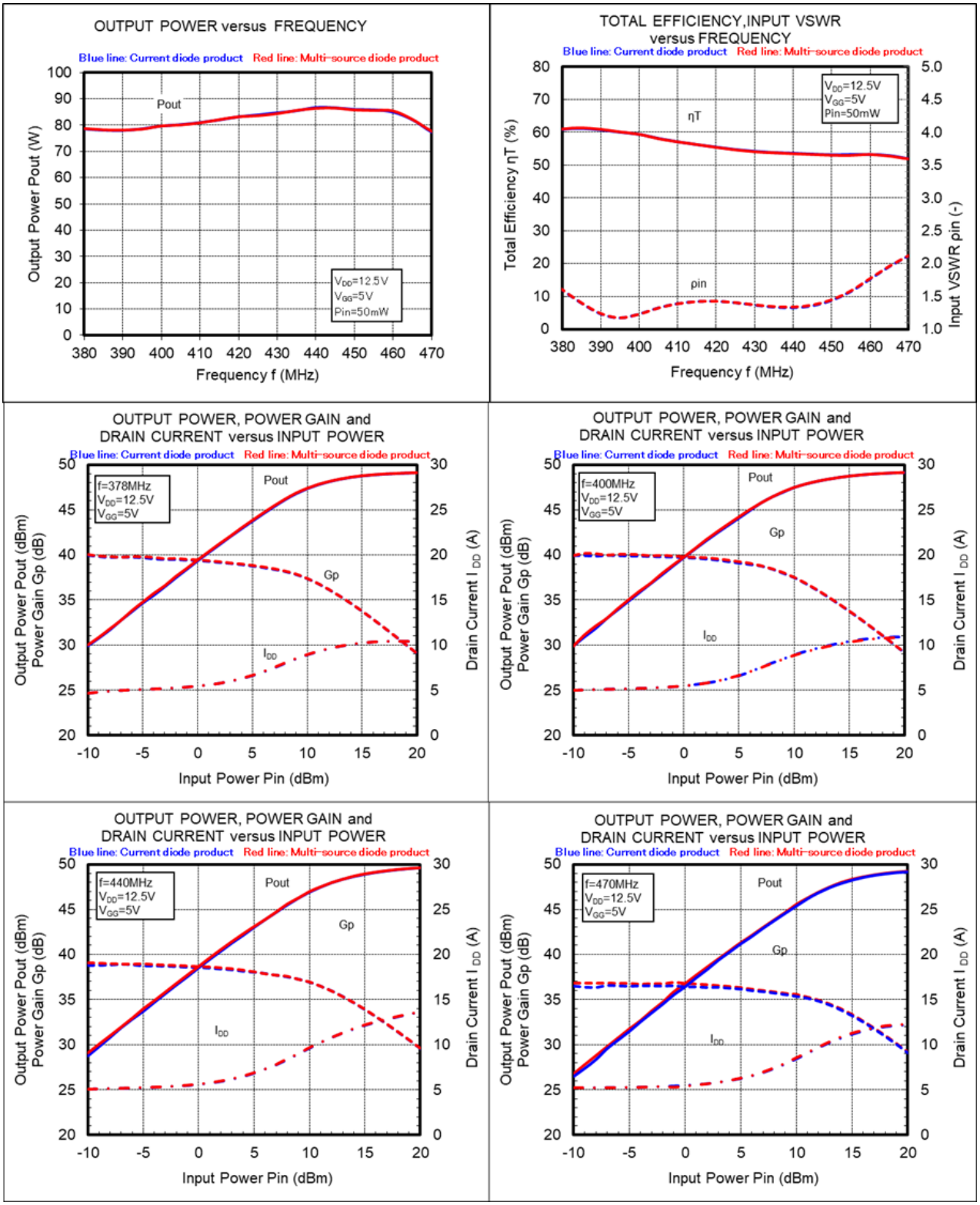

Fig.3-2 RF characteristics of RA60H3847M1-501 (Current diode, Multi-source diode)